# **UNR52A6G**

# Silicon NPN epitaxial planar type

## For digital circuits

#### ■ Features

- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- SMini type package allowing easy automatic insertion through tape packing

# ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
Collector current	$I_{\rm C}$	80	mA	
Total power dissipation	$P_{T}$	150	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

#### ■ Package

- Code
  - SMini3-F2
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

## ■ Marking Symbol: HD

#### ■ Internal Connection

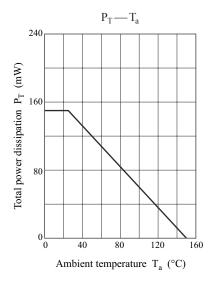
$$B \overset{R_1}{\circ} \overset{(4.7 \text{ k}\Omega)}{\checkmark} \overset{\circ}{\sim} C$$

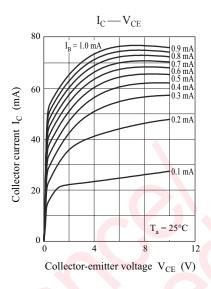
## ■ Electrical Characteristics T<sub>a</sub> = 25°C±3°C

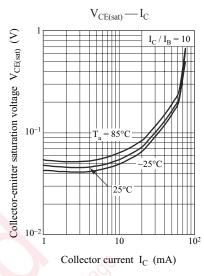
a		7 / 1 / 2 / 1/2 / 2/2 / 2 /	1 / /			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 6 \text{ V}, I_C = 0$			0.01	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	160		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = 5 \text{ V}, V_{B} = 0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = 5 \text{ V}, V_{B} = 2.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$			0.2	V
Input resistance	R <sub>1</sub>		-30%	4.7	+30%	kΩ
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

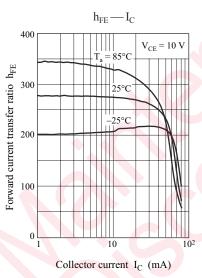
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

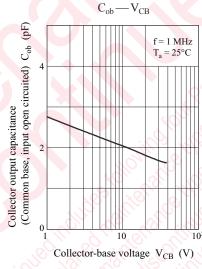
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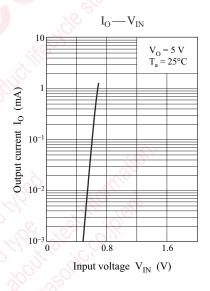


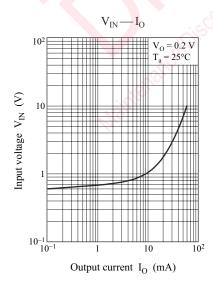




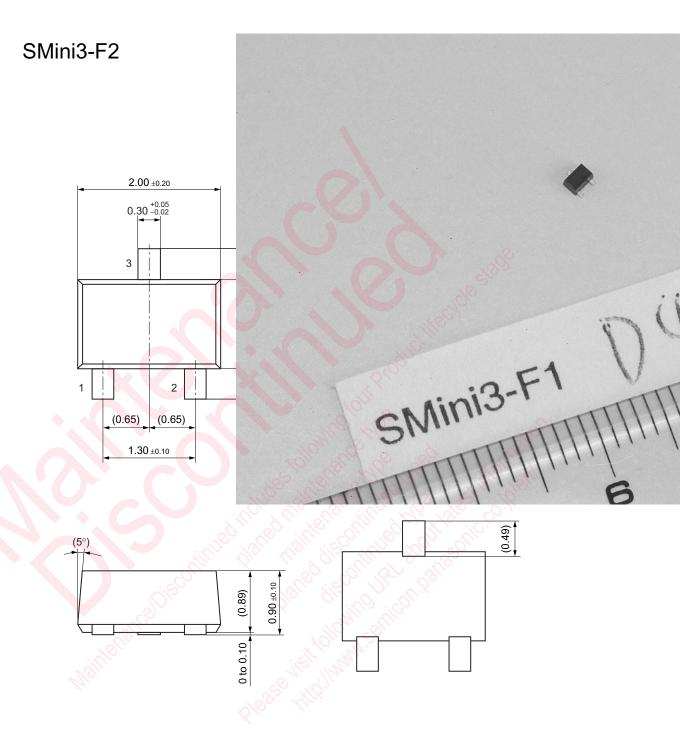








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